

Preparation, Properties and Applications of Chalcogenide Glasses

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- Non-oxide glasses: chalcogenide and chalcohalide glasses, their IR optical properties;
- Oxide glasses: scintillating glasses, luminescence glasses for LED lighting, quantum cutting effects;
- Radiation induced effects on glasses etc..
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References



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- 2. W.Vogel, Glass Chemistry, Springer-Verlag, 1992
- Journals: J. Non-Cryst. Solids,
 J. Am. Ceram. Soc., Chem. Phys.
 Lett., Chin. Phys. Lett., Appl.
 Phys. Lett., Opt. Lett., Opt.
 Express, Adv. Mater., etc.



Outline



- Generality
- Preparation
- Structure and properties
- Thermal treatment



• Main applications in passive and active infrared optics





The chalcogenide glasses (ChG)

- Named after the chalcogen elements including sulfur, selenium and tellurium.
- To be combined with various others, such as germanium and arsenic, to form stable glasses.



Element Periodic Table



Tracing Back



- **1870's** As₂S₃ glass formed
- **1950's ChG discovered as semiconductor**
- 1960'sChG used as IR transmitting
materials (passive applications)
- 1990'sActive applications interest for IRphotonic technologies



Passive Optics



The passive applications utilize chalcogenide fibers as a light conduit from one location to another without changing the optical properties.

> J. S. Sanghera, et al., *J. Non-Cryst. Solids*, 1999, 256-257:1-16







Active applications of chalcogenide glass fibers are where the initial light propagating through the fiber <u>is modified by a process</u>.



J. S. Sanghera, et al., *J. Non-Cryst. Solids*, 1999, 256-257:1-16

2. Preparation



Melting process





Quartz glass ampoule with batch

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Rocking furnace





Purification in order to remove impurities containing O, H and C

• Etching ampoule in hydrofluoric acid



- Distillations by heating the batch components in situ under vacuum
 - Addition of oxygen getter for examples, Zr, Al, Mg, Ca, Gd)

An exa Naval Research Laboratory USA





IR transmission spectra of As-Ge-Se-Te system glass under different purification conditions

- 1 Unpurified
- 2 Se purified
- 3 As, Se purified
- 4 As, Se, Te purified
- 5 Glass (3) distillated
- 6 Glass (4) distillated

J.S. Sanghera, et al., J. Non-Cryst. Solids, 1993, 161: 320-322



Purification conditions	Abs. coefficient α (cm ⁻¹ at 10.6 μ m)	Estimated O ₂ content (ppm wt)
Ge-As-Se system		
1 Unpurified	0.2030	144.2
2 As, Se purified	0.0991	3.1
3 Glass distillated	0.0454	1.3
Ge-As-Se-Te system		
1 Unpurified	0.1814	103.4
2 Se purified	0.1160	66.7
3 As, Se purified	0.0893	17.4
4 As, Se, Te purified	0.0308	5.6
5 Glass (3) distillated	0.0209	0.8
6 Glass (4) distillated	0.0071	0.6

3 Thermal Treatment



• Shortcoming of ChG: weak bond strength

$$v = 2\pi \sqrt{\frac{\kappa}{\mu}}$$



- v = vibration frequency
- $\kappa =$ force constant
 - $\mu = reduced mass of the$ vibrating ions $(\mu = m_c m_o/(m_c + m_o))$

Controlled crystallization



Key points:

- Glass composition
- Thermal treatment conditions



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Fang Xia, et al., J. Am. Ceram. Soc., 2006, 89(7) 2154-57

Crystallization ability



- VSG region where glasses with larger $\Delta T (> 170^{\circ}C, T_c - T_g)$, or no exothermal peak in DSC unable crystallized even for long time (>100 h) heating .
- Glasses near the border of glass forming region not thermally stable and tended to crystallize but very difficult to control crystal growth thus affecting IR transmission of materials.



Controlled crystallization



• Compositions suitable for controlled crystallization fall into dark shadow area which is classified as sub-stable glasses (SSG) region.



With these glasses under proper annealing conditions,
IR transmitting glass
ceramics with improved properties can be obtained.

SEM results





(a) P9 at 330°C for 163 h,
(b) P7 at 300°C for 5 h,
(c) P5 at 340°C for 15 h,
(d) P5 at 310°C for 15 h,
(e) P5 at 310°C for 32 h,
(f) P5 at 310°C for 85 h.

P5: 51GeS₂-9Sb₂S₃-40PbS P7: 30GeS₂-35Sb₂S₃-35PbS P9: 55GeS₂-30Sb₂S₃-15PbS

Crystal size: < 100 nm

IR transmittance



IR transmission of glass-ceramic beyond 2µm is nearly the same as the glass matrix.

Resistance to fracture







Glass-ceramics derived from SSG possess higher fracture toughness and lower thermal expansion coefficients.

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Controlled crystallization of GeSe₂-Ga₂Se₃-CsI ChGs during molding: (left) IR transmission spectra; (right) Resistance to crack propagation of (a) the base glass and (b) glass-ceramic

Wei Chen, et al., J. Am. Ceram. Soc., 2008, 91, 2720

4 Structure and Properties



A comparison of glassy-like A₂B₃ structure with crystalline one after Zachariasen



Feature of glass network: Short-range in order, longrange disorder

ChG can be classified by reference to dimensionality

- 1D spaghetti-type, such as Se glass made of infinite chains
- 2D distorted planar glasses such as As₂S₃ made from connections of 2
 coordinated S atoms and As 3 coordinated As atoms
- 3D glasses, such as GeSe₂ being result of GeSe₄ tetrahedra connections











Different from oxide glasses

- Narrower bandgap (1-3 eV)
 - semi-conducting
- Lower phonon energy (<350 cm⁻¹)
 - IR transmittance
- Photo-induced effects



Optical transmission







Evolution of the bandgap energy for GeSe₂-Ga₂Se₃ -CsCl glasses with 0, 10, 20, 30, and 40 mol% CsCl.

L. Calvez, et al., Adv. Mater. 2007, 19, 129





Grains homogeneous (ca. 100 nm) with uninfluenced FIR transmittance and the same *a*, and almost doubled toughness from 0.227 to 0.425.





Tellurium based glasses have excellent transmission in $3-20 \ \mu m$. Especially, Ge-As-Te system exhibits the best stability, more amenable for larger scale production.



P. Lucas, et al., J. Am. Ceram. Soc., 2009, 92, 2920



- PI dissolution (doping)
- PI refractive index (RI) change
- PI phase change
- PI bandgap energy change (darkening or bleaching)
- PI contraction
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T. Wagner, et al., Appl. Phys. Lett., 92 (2008)011114

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1.82 eV \implies 1.67 eV





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Schema of photo-induced phase change material KSb₅S₈

T. Kyratsi, et al., Adv. Mater., 2003,15(17):1429





pto-stable Se₅₅ films

Lapress, 2008,16:10565

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Effect of intensity on PI volume change in GeAsSe₁₃ glass. The annealed glass (black) shows PE, the quenched (red) PC. For large intensity, the latter eventually expansion.

L. Calvez, et al., Opt. Express, 2009,17:18581



- Passive optics
 - Laser transmission
 - Thermal imaging
- Active optics
 - Non-linear optics
 - •IR amplifier



Laser power delivery





(a)CO laser transmission, (b) CO_2 laser transmission and (c) pulsed high energy laser transmission in the 2-5 μ m region (±0.01 mW)

J. S. Sanghera, J. Non-Cryst. Solids, 1999, 256-257:6

Thermal imaging



TECHNOLOG





 Lower cost production by moulding compared with singlepoint diamond turning process
 for crystalline materials, e.g. Ge





Night-vision car





New 2006 BMW Series equiped with IR night-vision system with molded chalcogenide glass optics



IR transmission of GCs compared with $Ga_5Sb_{10}Ge_{25}Se_{60}$ glass

X. Zhang, et al., J. Non-Cryst. Solids, 2004, 336: 49

Molded lens





A molded GC lens (D=30 mm)

Molding precision: form defect of molded lenses by comparing the designed profile and the measured profile of the lens is $< 0.5 \mu m$.



light/fiber/amplifier/fiber/light



Matrix material is a key





Comparison of emission spectra between Ge-Ga-S glass and oxide glass doped with Pr³⁺ ions

Multiphonon relaxations (MPR)





$$W_{tot} = W_{rad} + W_{MP} + W_{ET} + \dots$$

Radiative Multiphonon Energy Transfer

• Quantum efficiency: $\eta = \frac{W_{rad}}{W_{rad} + W_{MP} + W_{ET}}$ $W_{MP} \uparrow with \uparrow phonon$ energy of the host



Pohang University of Science and Technology, Korea



J. Heo et al., Chem. Phys. Lett., 2000, 317: 637

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Raman spectra





Addition of CsBr resulted in a new lowphonon band at 245 cm⁻¹, associated with the Ga–Br bonds vibration, a major phonon mode determining the MPR process.

Normalized Intensity

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Broad NIR emission from Er³⁺-Tm³⁺ codoped 70GeS₂-20In₂S₃-10CsI glasses DIECHNOLOW

Yinsheng Xu et al., Opt. Lett., 2008, 33(20):2293

Shanghai Institute of Optics and Fine Mechanics, China ECUST, China





Emission spectra of Bi-Dy co-doped $70GeS_2-9.5Ga_2S_3-$ 20KBr chalcohalide glasses melted at the different temperature

Guang Yang, et al., J. Am. Ceram. Soc., 2007, 90, 3670

Shanghai Institute of Optics and Fine Mechanics, China Zhejiang University, China





Emission spectra of Bi-doped 80GeS₂-20Ga₂S₃ chalcogenide glasses

FWHM ~ 200 nm

Jianrong Qiu, et al., Chin. Phys. Lett., 2008, 25:1891

All-optical device (AOD)









All-optical dual core coupler (A) setup, (B) schematic dual core SiO₂ fiber, (C) two single-mode cores as waveguides.

Intensity of incoming light controls coupling from one core to the other.

Vogel E M, J. Am. Ceram. Soc., 1989, 72(5):719

Optical nonlinearity





With the higher susceptibility $\chi^{(3)}$ and SHG $\chi^{(2)}$, ChG photonic chips allow all-optical signal processing.

Plot of n₂ versus the term containing the normalized photon energy

J. S. Sanghera, et al., J. Non-Cryst. Solids, 2008, 354:462

Université de Rennes 1, France



$$n^{(2)} = 8.0 \text{ pm/V}$$

TECHNON

MF patterns of thermal poled Ge-Sb-S samples recorded for three temperatures: (a) 170°C and (b) 230°C (full line) and 310°C (dashed lines)

M. Guignarda, et al., Opt. Express, 2006, 14(4) 1528

Kyoto University, Japan ECUST, China





$$n^{(2)} = 7.0 \text{ pm/V}$$

Maker fringe of 60GeS₂-20Ga₂S₃-20KBr glass with higher alkali content after thermal poling

Jing Ren, et al., Opt. Lett., 2006, 31(23):3492

Wuhan University of Technology, China



$$n^{(2)} = 5.36-7.3 \text{ pm/V}$$

Maker fringe patterns of the β -GeS₂ crystallized glasses without poling treatment

Xiujian Zhao, et al., *Opt. Lett.*, 2009, 34(4):437

XRD and Raman spectra





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$$\chi^3 = 10.07 \times 10^{12}$$
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Optical Kerr Effect Siganl of GeSe₂-In₂Se₃-CsI glasses

Yinsheng Xu, et al., Phy. Chem. Lett., 2008, 462, 69-71

Raman spectra





[GeSe₄] at 200 cm⁻¹ and [InSe₄] at 154 cm⁻¹ are the main structural units while the increasing CsI does not cause clear structural



Optical Kerr Effect Siganl of As₂S₃ glass before and after laser radiation

Lei Xu, et al., Appl. Phy. Lett., 2007, 91, 181917





- Purification is an important procedure for synthesis of high purity ChGs.
- Controlled crystallization is an effective way to improve mechanical and thermal properteis of ChGs.
- Different from oxide glasses, ChGs have narrower bandgap, lower phonon energy, and are photosensitive.
- ChGs are potential for applications in active optics due to unique IR optical properties.



Thank You for Your Attention

